



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	Ι _D T _A = +25°C
201/	25mΩ @ V _{GS} = -10V	-6.8A
-30V	$38m\Omega @ V_{GS} = -4.5V$	-5.0A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

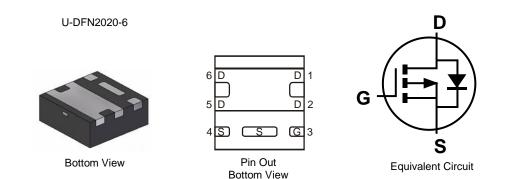
- **DC-DC Converters**
- **Power Management Functions**
- Load Switch

Features

- Low Input Capacitance •
- Low On-Resistance •
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 •
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.0065 grams (Approximate)



Ordering Information (Note 4)

	Part Number	Case	Packaging			
	DMP3028LFDE-7	U-DFN2020-6	3,000/Tape & Reel			
	DMP3028LFDE-13	U-DFN2020-6	10,000/Tape & Reel			
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.					

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



PX = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011)M = Month (ex: 9 = September)

Date Code Kev

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Y		Z		А	E	3	С		D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current (Note C) // 10//	Steady State	T _A = +25°C T _A = +70°C	ID	-6.8 -5.3	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t<10s	T _A = +25°C T _A = +70°C	ID	-8.2 -6.6	А
Maximum Body Diode Forward Current (Note 6)	Is	-2.5	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-40	А		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Dawar Dissinction (Nata 5)	T _A = +25°C	P	0.66	W
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.42	
Thermal Registeres, Junction to Ambient (Note 5)	Steady State	D	189	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	125	
Total Dower Dissinction (Note 6)	T _A = +25°C	Р	2.03	W
Total Power Dissipation (Note 6)	T _A = +70°C	PD	1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	61	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ ext{ heta}JA}$	41	
Thermal Resistance, Junction to Case (Note 6)		$R_{ ext{ heta}JC}$	9.3	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

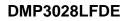
	-	1		r		
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-1.2		-2.4	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
Static Drain-Source On-Resistance	D		20	25	mΩ	$V_{GS} = -10V, I_D = -7A$
Static Drain-Source On-Resistance	R _{DS (ON)}		29	38	11122	$V_{GS} = -4.5V, I_D = -6.2A$
Forward Transfer Admittance	Y _{fs}		4.5	—	S	$V_{DS} = -5V, I_D = -7A$
Diode Forward Voltage	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = -2.1A$
On State Drain Current (Note 8)	ID(ON)	-20	_	_	Α	$V_{DS} \leq -5V, V_{GS} = -4.5V$
DYNAMIC CHARACTERISTICS (Note 8)				•		
Input Capacitance	C _{iss}		1241	1860		
Output Capacitance	Coss		147	220	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		110	165		I = 1.00012
Gate Resistance	R _G	_	15	30	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg		22	33		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	10.9	17	-0	
Gate-Source Charge	Q _{gs}	_	3.5	6	nC	$V_{DS} = -15V, I_D = -7A$
Gate-Drain Charge	Q _{gd}	_	4.7	8		
Turn-On Delay Time	t _{D(on)}		9.7	15		
Turn-On Rise Time	tr		17.1	26	nS	$V_{GS} = -10V, V_{DD} = -15V, R_{GEN} = 6\Omega,$
Turn-Off Delay Time	t _{D(off)}		60.5	91	115	I _D = -7A
Turn-Off Fall Time	tf		40.4	61		

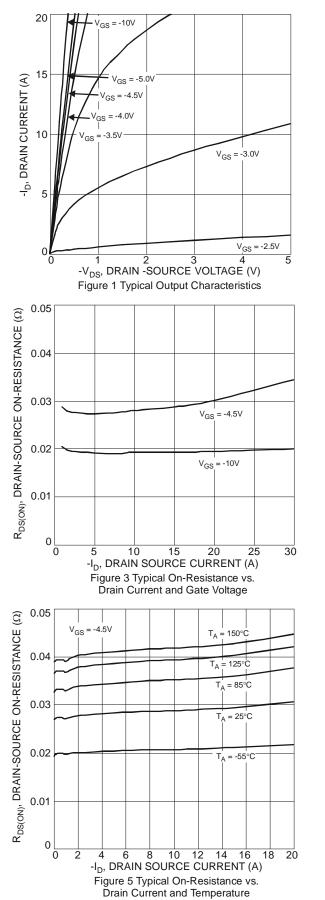
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

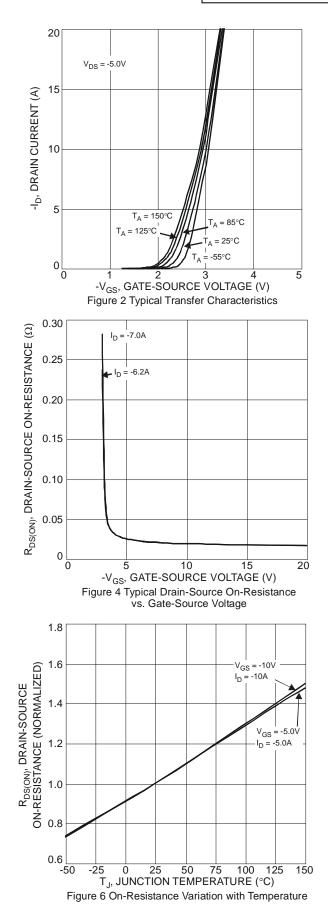
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.









-I_D = 1mA

i_D = 250µA

50

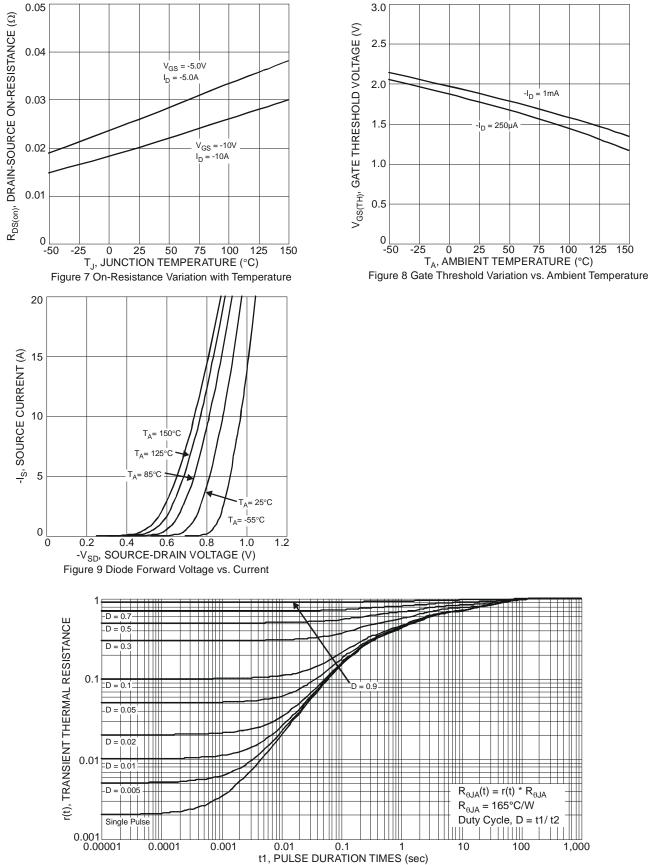
100

1,000

75

100 125 150

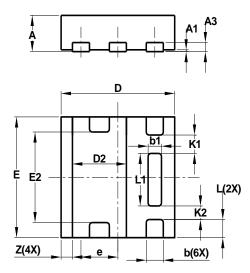






Package Outline Dimensions

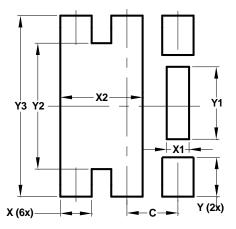
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6								
Туре Е								
Dim	Min Max Ty							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
Е	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	-	-	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1	-	_	0.305					
K2	-	-	0.225					
Z	-	-	0.20					
All	Dimens	ions in I	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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